



STPS80L15CY

LOW DROP OR-ing POWER SCHOTTKY RECTIFIER

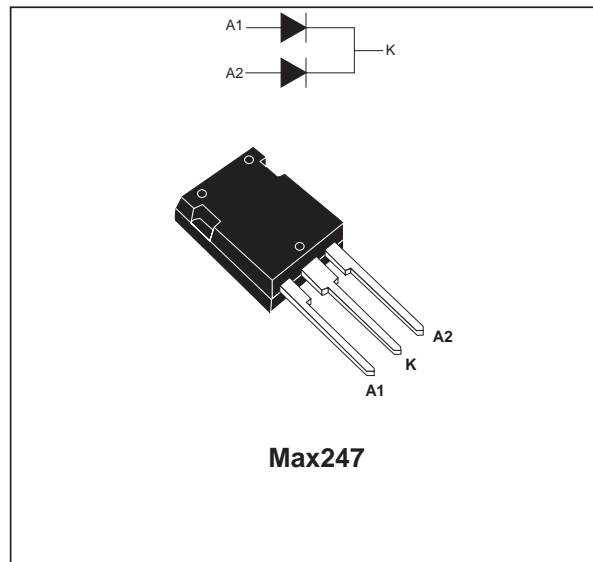
PRELIMINARY DATASHEET

MAIN PRODUCT CHARACTERISTICS

I_{F(AV)}	2 x 40 A
V_{RRM}	15 V
T_j (max)	125 °C
V_F (max)	0.33 V

FEATURES AND BENEFITS

- Max247 PACKAGE, DUAL DIODE CONSTRUCTION, 2 x 40A
- 15V BLOCKING VOLTAGE SUITABLE FOR 5V AND 12V OR-ing
- EXTREMELY LOW VOLTAGE VOLTAGE DROP: 0.33V @ 100°C
- OPERATING JUNCTION TEMPERATURE: 125°C
- AVALANCHE CAPABILITY SPECIFIED



DESCRIPTION

The STPS80L15CY uses proprietary barrier technology to optimize forward voltage drop for OR-ing functions in n-1 fault tolerant Switch Mode Power Supplies.

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive peak reverse voltage	15	V
I _{F(RMS)}	RMS forward current	50	A
I _{F(AV)}	Average forward current	T _c = 110°C δ = 0.5 Per diode: 40 Per device: 80	A
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoidal	400 A
I _{RRM}	Repetitive peak reverse current	t _p = 2 μs F = 1kHz square	2 A
P _{ARM}	Repetitive peak avalanche power	t _p = 1μs T _j = 25°C	36045 W
T _{stg}	Storage temperature range	- 65 to + 150	°C
T _j	Maximum operating junction temperature	125	°C
dV/dt	Critical rate of rise of reverse voltage	10000	V/μs

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{th(j-c)}	Junction to case	Per diode	0.7	°C/W
		Total	0.5	
R _{th(c)}		Coupling	0.3	

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	T _j = 25°C	V _R = 5V			4	mA
		T _j = 100°C			280	400	
		T _j = 25°C	V _R = 12V			11	A
		T _j = 100°C			0.44	1.1	
		T _j = 25°C	V _R = 15V			16	mA
		T _j = 100°C			0.53	1.3	
V _F *	Forward voltage drop	T _j = 25°C	I _F = 40 A			0.42	V
		T _j = 100°C	I _F = 40 A		0.30	0.33	
		T _j = 25°C	I _F = 80 A			0.55	
		T _j = 100°C	I _F = 80 A		0.40	0.46	

Pulse test : * t_p = 380 μs, δ < 2%

To evaluate the maximum conduction losses use the following equation :

$$P = 0.20 \times I_{F(AV)} + 0.0032 \times I_{F(RMS)}^2$$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

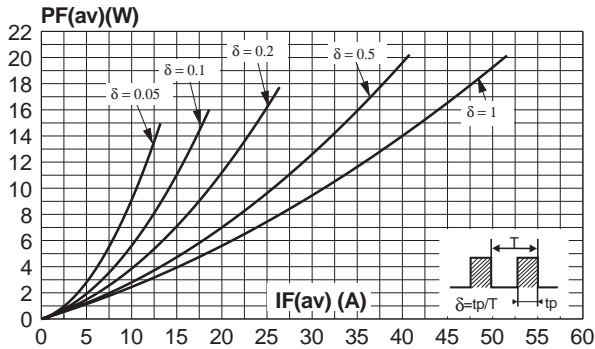


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$, per diode).

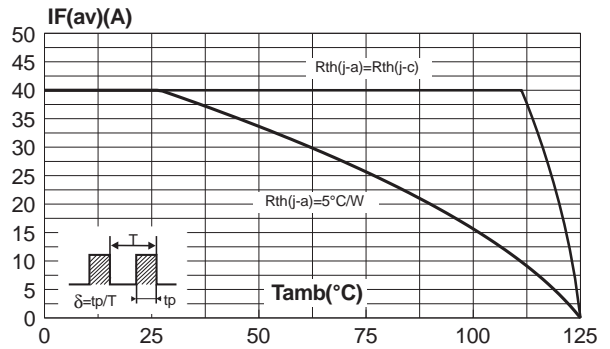


Fig. 3: Normalized avalanche power derating versus pulse duration.

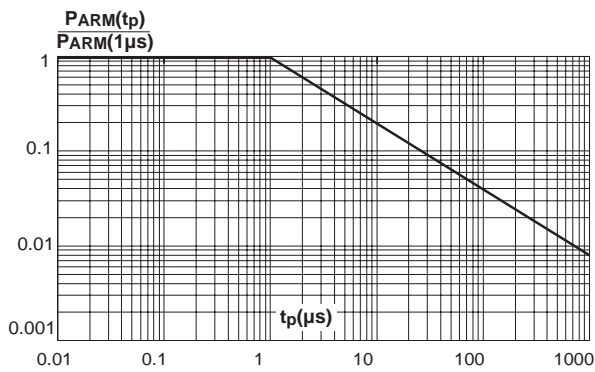


Fig. 4: Normalized avalanche power derating versus junction temperature.

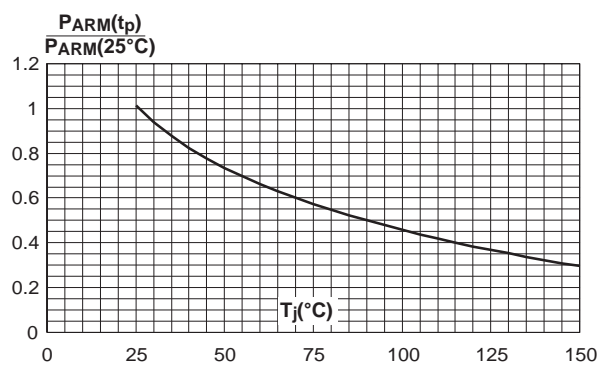


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).

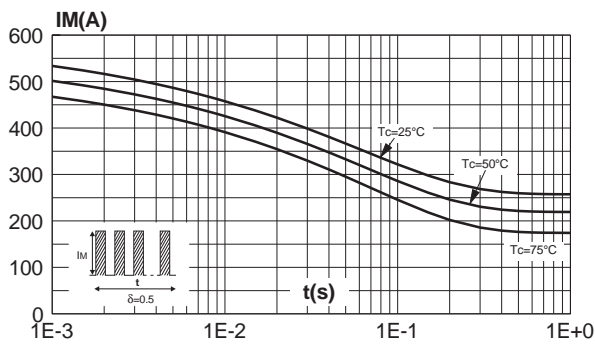


Fig. 6: Relative variation of thermal impedance junction to case versus pulse (per diode).

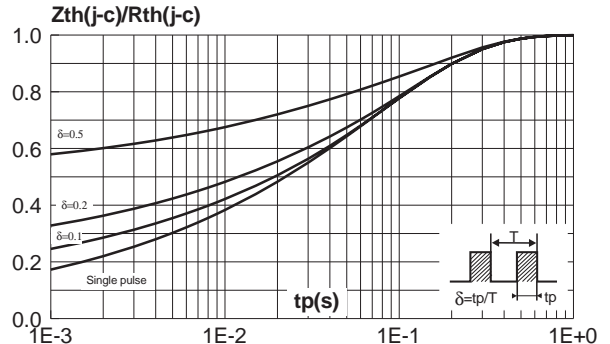


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values, per diode).

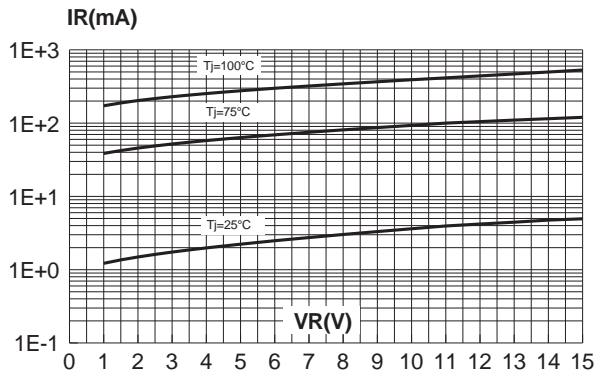


Fig. 8: Junction capacitance versus reverse voltage applied (typical values, per diode).

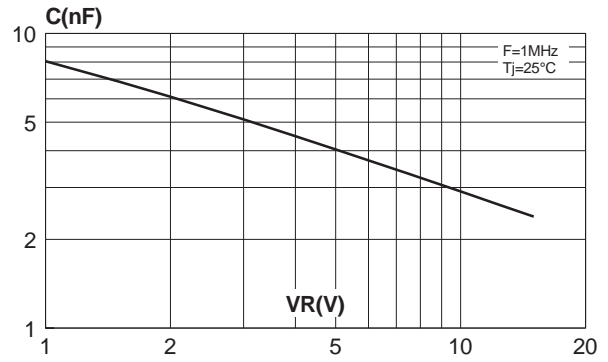
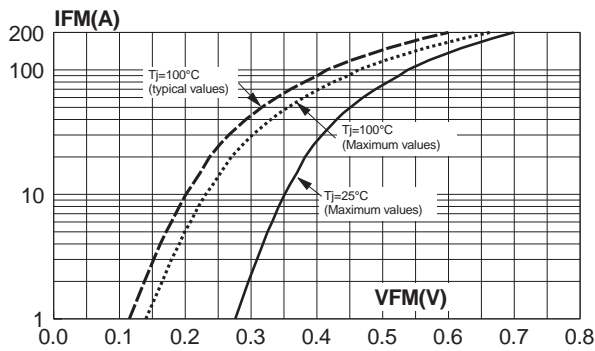
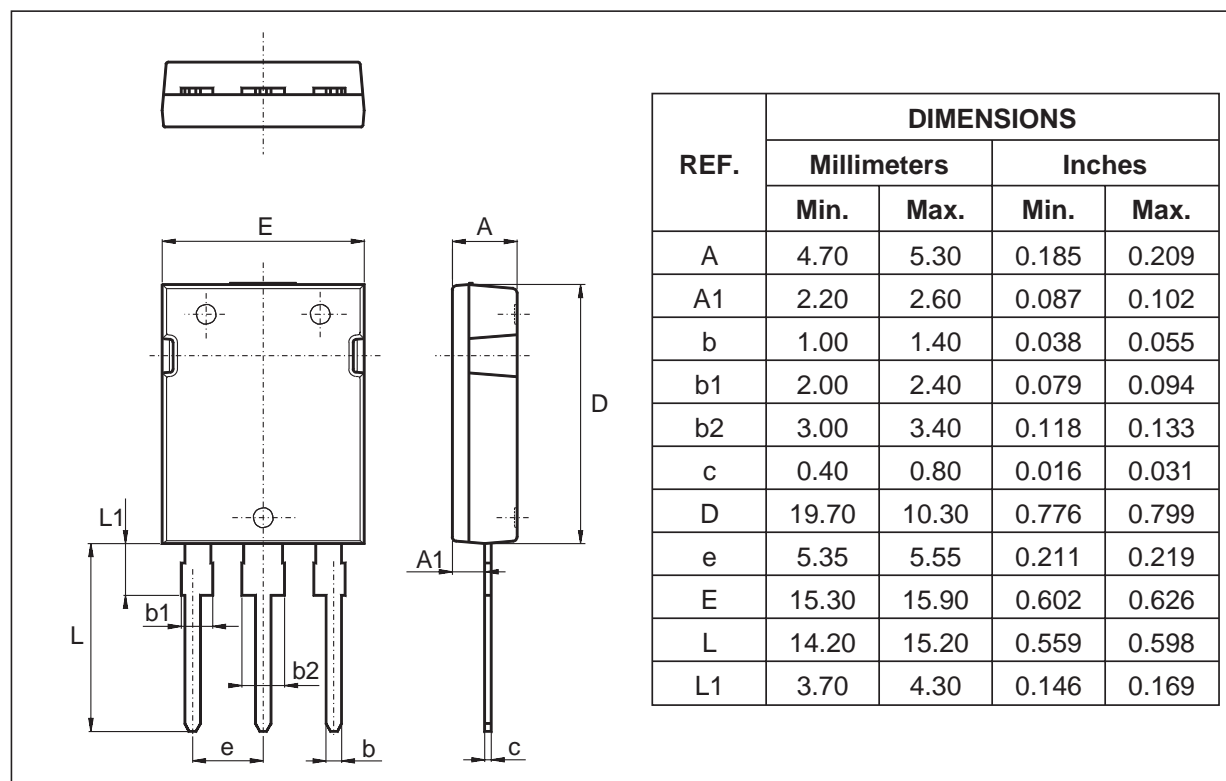


Fig. 9: Forward voltage drop versus forward current (per diode).



PACKAGE MECHANICAL DATA

Max247



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS80L15CY	STPS80L15CY	Max247	4.4g	30	Tube

- Cooling method: by conduction (C)
- Epoxy meets UL94,V0

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